L Number	Hits	Search Text	DB	Time stamp
1	68	(coat coating deposit depositing deposition film layer	USPAT;	2004/03/11 17:57
		layering) near3 (silicon near (carbide nitride oxide dioxide)	US-PGPUB;	
		"si.sub.3.N.sub.4" "si.sub.3 n.sub.4" "sio.sub.2" "si O.sub.2"	EPO; JPO;	
		"SiC" "Si C") and ((438/121,122,for.436).CCLS.) and	DERWENT;	
		pd>=20031124	IBM_TDB	
-	2	("20020121698").PN.	USPAT;	2004/03/11 13:45
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	2	("6369452").PN.	USPAT;	2004/03/11 15:30
	_	()	US-PGPUB;	, ,
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	2	("4939316").PN.	USPAT;	2004/03/11 15:34
	_	(US-PGPUB;	, ,
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
<u>-</u>	2	("5066368").PN.	USPAT;	2004/03/11 15:34
	_	(555555)	US-PGPUB;	, ,
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
l _	1664	deposit\$3 near4 (insultaing insulator silicon near (oxide	USPAT;	2004/03/11 16:35
	100.	dioxide nitrid carbide)) with (heat nea (slug sink plate))	US-PGPUB;	
1			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
_	656	deposit\$3 near4 (insultaing insulator silicon near (oxide	USPAT;	2004/03/11 17:03
		dioxide nitrid carbide)) near4 (heat nea (slug sink plate))	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
] -	0	deposit\$3 near4 (insultaing insulator silicon near (oxide	USPAT;	2004/03/11 17:03
İ		dioxide nitrid carbide)) near4 (heat near (slug sink plate))	US-PGPUB;	
		not (deposit\$3 near4 (insultaing insulator silicon near (oxide	EPO; JPO;	
	1	dioxide nitrid carbide)) near4 (heat nea (slug sink plate)))	DERWENT;	
			IBM_TDB	
l -	0	deposit\$3 near4 (insultaing insulator silicon near (oxide	USPAT;	2004/03/11 17:04
		dioxide nitrid carbide)) near4 ((metal metallic) near (slug	US-PGPUB;	1
	1	sink plate)) not (deposit\$3 near4 (insultaing insulator silicon	EPO; JPO;	
		near (oxide dioxide nitrid carbide)) near4 (heat nea (slug	DERWENT;	
1		sink plate)))	IBM_TDB	1